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INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

				Complete If Known
Application Number				10/667,615
Filing Date				09/22/03
First Named Inventor				Theodore W. Houston
Group Art Unit				2811
Examiner Name				Douglas W. Owens
Sheet	1	of	1	Attorney Docket No. TI-35657

U.S. PATENT DOCUMENTS

Exam. Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
AA	6,396,108			Krivokapic et al.	5/28/02	
AB	6,307,230			Chatterjee et al.	10/23/01	
AC	6,225,175			Houston	5/1/01	
AD						
AE						
AF						
AG						
AH						
AI						
AJ						
AK						
AL						

FOREIGN PATENT DOCUMENTS

Exam. Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ² (if known)				
BA	WO	02/103703 A2			Innovative Silicon SA	12/27/02		
BB								
BC								
BD								
BE								
BF								
BG								

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Exam. Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
CA	KAZUMI INOH, ET AL., "FBC (Floating Body Cell) for Embedded DRAM on SOI" 2003 Symposium on VLSI Technology Digest of Technical Papers, pp. 1-2		
CB	TAKASHI OHSAWA, ET AL., "A Memory Using One-Transistor Gain Cell on SOI (FBC) with Performance Suitable for Embedded DRAM's" 2003 Symposium on VLSI Circuits Digest of Technical Papers, pp. 1-4		
CC	B. DOYLE, ET AL., "Tri-Gate Fully-Depleted CMOS Transistors: Fabrication, Design and Layout" 2003 Symposium on VLSI Technology Digest of Technical Papers, pp. 1-2		
CD			
CE			
CF			
CG			

Examiner Signature		Date Considered	
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